



FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16386

Generic Copy

18-Feb-2010

TITLE: MOSFET TO220 Products to Nantong-Fujitsu Microelectronics Co.

PROPOSED FIRST SHIP DATE: 15-May-2010

AFFECTED CHANGE CATEGORY(S): MOSFET Backend Manufacturing

FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:

Contact your local ON Semiconductor Sales Office or Dianne von Borstel
<d.von.borstel@onsemi.com>

SAMPLES: Contact your local ON Semiconductor Sales Office or Brian Goodburn
<brian.goodburn@onsemi.com>

ADDITIONAL RELIABILITY DATA: Available

Contact your local ON Semiconductor Sales Office or Donna Scheuch <d.scheuch@onsemi.com>

NOTIFICATION TYPE:

Final Product/Process Change Notification (FPCN)

Final change notification sent to customers. FPCNs are issued at least 90 days prior to implementation of the change.

ON Semiconductor will consider this change approved unless specific conditions of acceptance are provided in writing within 30 days of receipt of this notice. To do so, contact <quality@onsemi.com>.

DESCRIPTION AND PURPOSE:

This is a notification that ON Semiconductor will be using Nantong Fujitsu Microelectronics Co. (NFME) as a TO220 manufacturing facility for their MOSFET products. NFME's TO220 package does meet the JEDEC case outline. The Product portfolio, which will be assembled and electrically tested at NFME, will be included in the Device list with this notification.

In addition to NFME, ON Semiconductor will continue to manufacture TO220 products at their current external subcontractor, Pacific Semiconductor Inc (PSI) located in the Philippines.

**FINAL PRODUCT/PROCESS CHANGE NOTIFICATION #16386****RELIABILITY DATA SUMMARY:****Reliability Test Results: NTP5426G**

Test: High Temperature Reverse Bias (HTRB)
Conditions: Vds= 80% Vds rating, Ta=175°C, 1008-Hrs
Results: 0/240

Test: High Temperature Gate Bias (HTGB)
Conditions: Vgs= 100% Vgs rating, Ta=175°C, 1008-Hrs.
Results: 0/240

Test: High Humidity, High Temperature Reverse Bias (H3TRB)
Conditions: Vds= 24Vds, Ta=85°C, Rel Humidity = 85%, 1008-Hrs
Results: 0/240

Test: High Accelerated Stress Test (HAST)
Conditions: Vds= 24Vds, P= 18.8psig, Ta=131°C, RH = 85%, 96-Hrs
Results: 0/240

Test: High Accelerated Stress Test (uHAST)
Conditions: P= 15g, Ta=12°C, RH = 10096-Hrs
Results: 0/231

Test: Intermittent Operating Life (IOL-PC)
Conditions: Ta=+25°C, delta Tj=100°C, 2-min on/off, 15K-cycles
Results: 0/240

Test: Temperature Cycling (TC-PC)
Conditions: Ta=-65°C/+150°C, Air-to-Air, Dwell >=10-min, 1000-cy
Results: 0/240

ELECTRICAL CHARACTERISTIC SUMMARY:

There is no change in electrical parametric performance. Characterization data is available upon request.

CHANGED PART IDENTIFICATION:

TO220 Product manufactured for ON Semiconductor at Nantong Fujitsu Microelectronics Co. (NFME) will be marked with 'N'

TO220 Product manufactured for ON Semiconductor at Pacific Semiconductor Inc. (PSI) will be marked with 'Q'



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List of affected General Parts:

MTP10N10EL
MTP10N10ELG
MTP12P10
MTP12P10G
MTP20N15E
MTP20N15EG
MTP23P06V
MTP23P06VG
MTP2P50E
MTP2P50EG
MTP50P03HDL
MTP50P03HDLG
MTP75N05HD
NTP125N02R
NTP125N02RG
NTP13N10
NTP13N10G
NTP18N06
NTP18N06G
NTP18N06L
NTP18N06LG
NTP27N06G
NTP2955
NTP2955G
NTP30N06L
NTP30N06LG
NTP30N20
NTP30N20G
NTP35N15
NTP35N15G
NTP4302
NTP4302G
NTP45N06
NTP45N06G
NTP45N06L
NTP45N06LG
NTP52N10
NTP52N10G
NTP5411NG
NTP5426NG
NTP60N06
NTP60N06G
NTP60N06L
NTP60N06LG
NTP65N02R
NTP65N02RG
NTP75N03-006
NTP75N03L09
NTP75N03L09G
NTP75N03RG
NTP75N06
NTP75N06G
NTP85N03G
NTP90N02G